Syntez Microelectronics

KT9156AC

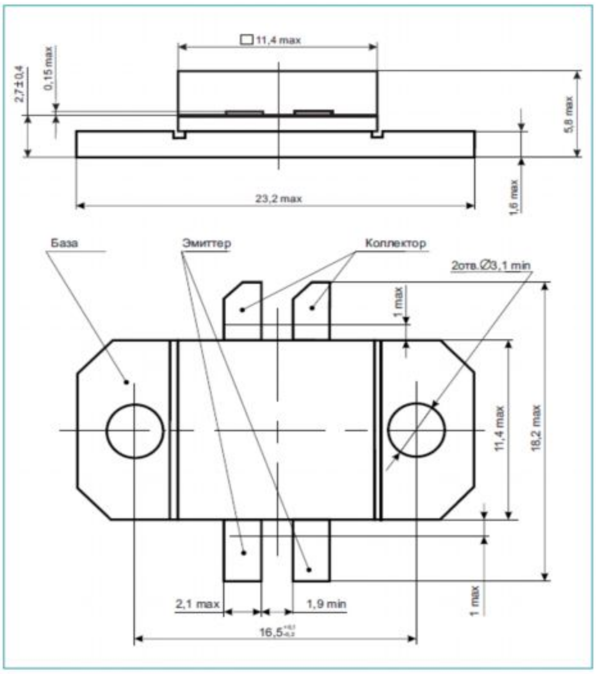
NPN SILICON RF POWER TRANSISTOR

Designed for wideband large-signal
Class AB linear amplifier applications
in power FM equipment operating to 1GHz

- Output power = 15 W, f = 1000 MHz, V_{CC} = 28 V
- Power gain = 7 dB (min)
- Efficiency = 40% (min)

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CER}	50	V
Emitter-Base Voltage	V_{EBO}	3	V
Collector Current	I_C	4	A
Operating Junction Temperature	T_j	+200	°C
Storage Temperature Range	T_{stg}	-65 to +150	°C
Thermal Resistance (junction to case)	$R_{\theta JC}$	3.2	°C/W
Total Power Dissipation, T_C=25 °C	P_D	55	W



Case KT-44

FUNCTIONAL TESTS

Characteristics	Symbol	Value			Unit
		min	typ	max	
Common-Emitter Amplifier Power Gain (V_{cc} = 28 V, P_{out} = 15 W @ 1 dB Comp., f = 1000 MHz)	G_P	7			dB
Collector Efficiency (V_{cc} = 28 V, P_{out} = 15 W, f = 1000 MHz)	η_C	40			%

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